

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A semiconductor device, comprising:

a plurality of fin structures comprising a crystalline silicon material formed from amorphous silicon using metal-induced crystallization (MIC);

a source region formed at one end of the fin structures;

a drain region formed at an opposite end of the fin structures; and

at least one gate.
2. (Original) The semiconductor device of claim 1, wherein a width of each of the fin structures ranges from about 100 Å to about 1000 Å.
3. (Original) The semiconductor device of claim 1, wherein the plurality of fin structures is two fin structures.
4. (Original) The semiconductor device of claim 1, wherein a pitch associated with the fin structures is about 600 Å.
5. (Original) The semiconductor device of claim 1, wherein a height of each of the fin structures ranges from about 500 Å to about 2000 Å.

6-14. (Canceled)

15. (Currently amended) A semiconductor device, comprising:

a substrate;

a plurality of crystalline silicon fin structures formed on the substrate from amorphous silicon using metal-induced crystallization (MIC), a center-to-center distance between each of the fin structures being about 600 Å;

a source region formed at one end of the fin structures;

a drain region formed at an opposite end of the fin structures; and

one or more gates.

16. (Original) The semiconductor device of claim 15, wherein a width of each of the fin structures ranges from about 100 Å to about 1000 Å.

17. (Original) The semiconductor device of claim 15, wherein the plurality of fin structures is two fin structures.

18. (Original) The semiconductor device of claim 15, wherein the plurality of fin structures is more than two fin structures.

19. (Original) The semiconductor device of claim 15, wherein a height of each of the fin structures ranges from about 500 Å to about 2000 Å.

20. (New) A semiconductor structure, comprising:
- a plurality of fins formed on a substrate from amorphous silicon; and
- a metal layer formed on surfaces of the plurality of fins, wherein the metal layer is annealed to diffuse the metal layer into the amorphous silicon and convert the amorphous silicon to crystalline silicon.
21. (New) The semiconductor structure of claim 20, wherein the metal layer comprises nickel.
22. (New) The semiconductor structure of claim 20, wherein the metal layer has a thickness of about 20 Å.